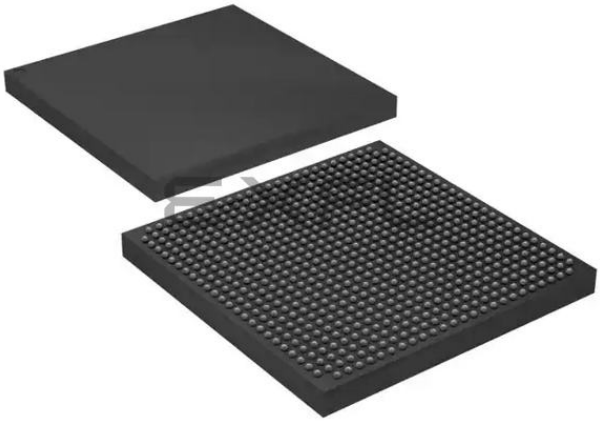

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	1846
Number of Logic Elements/Cells	18460
Total RAM Bits	1669248
Number of I/O	426
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep1s20f672i7n

Table 1–1. Stratix Device Features — EP1S10, EP1S20, EP1S25, EP1S30

Feature	EP1S10	EP1S20	EP1S25	EP1S30
LEs	10,570	18,460	25,660	32,470
M512 RAM blocks (32 × 18 bits)	94	194	224	295
M4K RAM blocks (128 × 36 bits)	60	82	138	171
M-RAM blocks (4K × 144 bits)	1	2	2	4
Total RAM bits	920,448	1,669,248	1,944,576	3,317,184
DSP blocks	6	10	10	12
Embedded multipliers *(1)*	48	80	80	96
PLLs	6	6	6	10
Maximum user I/O pins	426	586	706	726

Table 1–2. Stratix Device Features — EP1S40, EP1S60, EP1S80

Feature	EP1S40	EP1S60	EP1S80
LEs	41,250	57,120	79,040
M512 RAM blocks (32 × 18 bits)	384	574	767
M4K RAM blocks (128 × 36 bits)	183	292	364
M-RAM blocks (4K × 144 bits)	4	6	9
Total RAM bits	3,423,744	5,215,104	7,427,520
DSP blocks	14	18	22
Embedded multipliers *(1)*	112	144	176
PLLs	12	12	12
Maximum user I/O pins	822	1,022	1,238

Note to Tables 1–1 and 1–2:

(1) This parameter lists the total number of 9 × 9-bit multipliers for each device. For the total number of 18 × 18-bit multipliers per device, divide the total number of 9 × 9-bit multipliers by 2. For the total number of 36 × 36-bit multipliers per device, divide the total number of 9 × 9-bit multipliers by 8.

Table 2–11. M-RAM Combined Byte Selection for ×144 Mode Notes (1), (2)	
byteena[15..0]	**datain ×144**
[0] = 1	[8..0]
[1] = 1	[17..9]
[2] = 1	[26..18]
[3] = 1	[35..27]
[4] = 1	[44..36]
[5] = 1	[53..45]
[6] = 1	[62..54]
[7] = 1	[71..63]
[8] = 1	[80..72]
[9] = 1	[89..81]
[10] = 1	[98..90]
[11] = 1	[107..99]
[12] = 1	[116..108]
[13] = 1	[125..117]
[14] = 1	[134..126]
[15] = 1	[143..135]

Notes to Tables 2–10 and 2–11:

(1) Any combination of byte enables is possible.

(2) Byte enables can be used in the same manner with 8-bit words, i.e., in ×16, ×32, ×64, and ×128 modes.

Similar to all RAM blocks, M-RAM blocks can have different clocks on their inputs and outputs. All input registers—`renwe`, `datain`, address, and byte enable registers—are clocked together from either of the two clocks feeding the block. The output register can be bypassed. The eight `labclk` signals or local interconnect can drive the control signals for the A and B ports of the M-RAM block. LEs can also control the `clock_a`, `clock_b`, `renwe_a`, `renwe_b`, `clr_a`, clr_b, `clocken_a`, and `clocken_b` signals as shown in Figure 2–19.

Table 2–12 shows the input and output data signal connections for the column units (B1 to B6 and A1 to A6). It also shows the address and control signal input connections to the row units (R1 to R11).

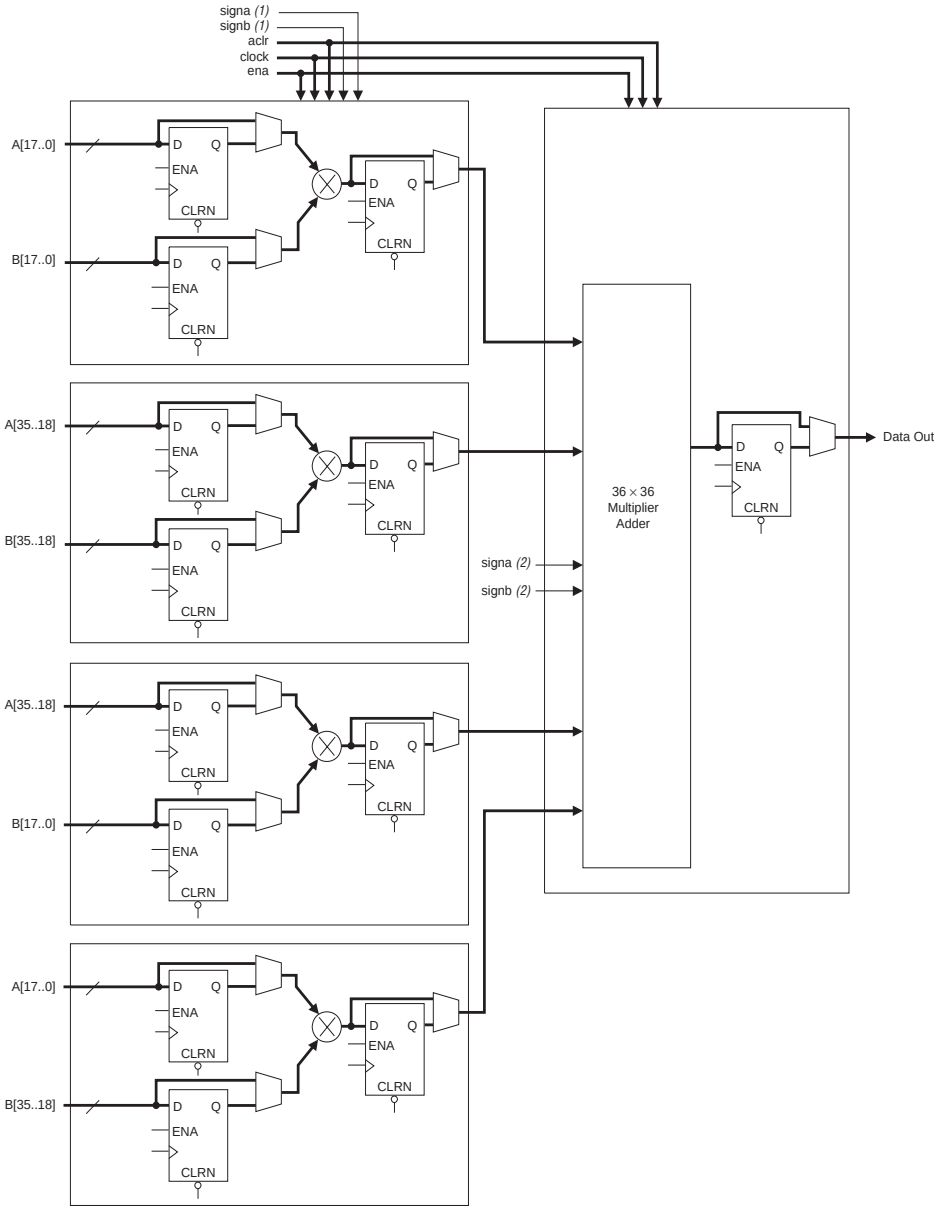
Table 2–12. M-RAM Row & Column Interface Unit Signals

Unit Interface Block	Input SIgnals	Output Signals
R1	addressa[7..0]	
R2	addressa[15..8]	
R3	byte_enable_a[7..0] renwe_a	
R4	-	
R5	-	
R6	clock_a clocken_a clock_b clocken_b	
R7	-	
R8	-	
R9	byte_enable_b[7..0] renwe_b	
R10	addressb[15..8]	
R11	addressb[7..0]	
B1	datain_b[71..60]	dataout_b[71..60]
B2	datain_b[59..48]	dataout_b[59..48]
B3	datain_b[47..36]	dataout_b[47..36]
B4	datain_b[35..24]	dataout_b[35..24]
B5	datain_b[23..12]	dataout_b[23..12]
B6	datain_b[11..0]	dataout_b[11..0]
A1	datain_a[71..60]	dataout_a[71..60]
A2	datain_a[59..48]	dataout_a[59..48]
A3	datain_a[47..36]	dataout_a[47..36]
A4	datain_a[35..24]	dataout_a[35..24]
A5	datain_a[23..12]	dataout_a[23..12]
A6	datain_a[11..0]	dataout_a[11..0]

Read/Write Clock Mode

The memory blocks implement read/write clock mode for simple dual-port memory. You can use up to two clocks in this mode. The write clock controls the block's data inputs, `wraddress`, and `wren`. The read clock controls the data output, `rdaddress`, and `rden`. The memory blocks support independent clock enables for each clock and asynchronous clear signals for the read- and write-side registers. Figure 2–27 shows a memory block in read/write clock mode.

Figure 2–36. 36 × 36 Multiply Mode

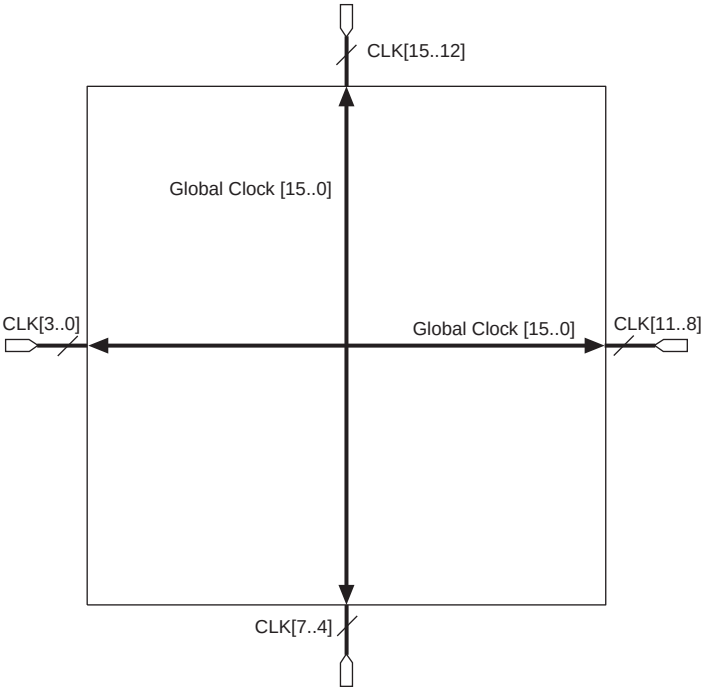


Notes to Figure 2–36:

(1) These signals are not registered or registered once to match the pipeline.

(2) These signals are not registered, registered once, or registered twice for latency to match the pipeline.

Figure 2–42. Global Clocking Note (1)



Note to Figure 2–42:

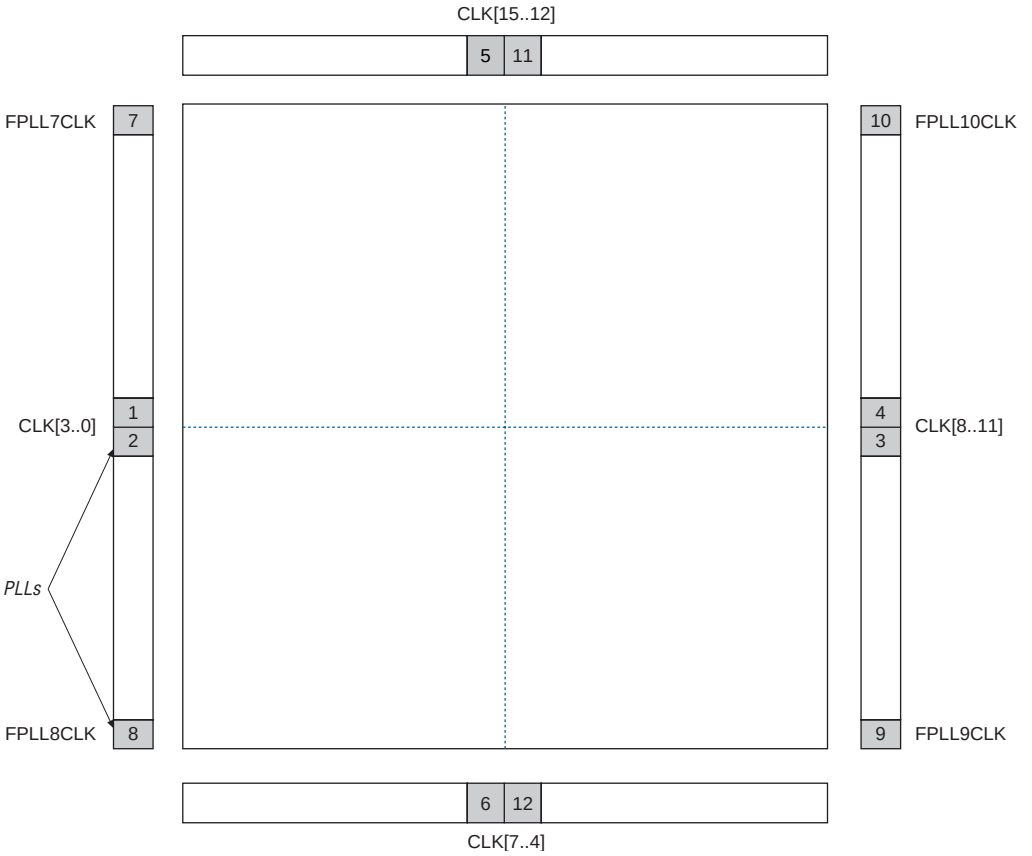
(1) The corner fast PLLs can also be driven through the global or regional clock networks. The global or regional clock input to the fast PLL can be driven by an output from another PLL, a pin-driven global or regional clock, or internally-generated global signals.

Regional Clock Network

There are four regional clock networks within each quadrant of the Stratix device that are driven by the same dedicated CLK[15..0] input pins or from PLL outputs. From a top view of the silicon, RCLK[0..3] are in the top left quadrant, RCLK[8..11] are in the top-right quadrant, RCLK[4..7] are in the bottom-left quadrant, and RCLK[12..15] are in the bottom-right quadrant. The regional clock networks only pertain to the quadrant they drive into. The regional clock networks provide the lowest clock delay and skew for logic contained within a single quadrant. RCLK cannot be driven by internal logic. The CLK clock pins symmetrically drive the RCLK networks within a particular quadrant, as shown in Figure 2–43. See Figures 2–50 and 2–51 for RCLK connections from PLLs and CLK pins.

Figure 2–49 shows a top-level diagram of the Stratix device and PLL floorplan.

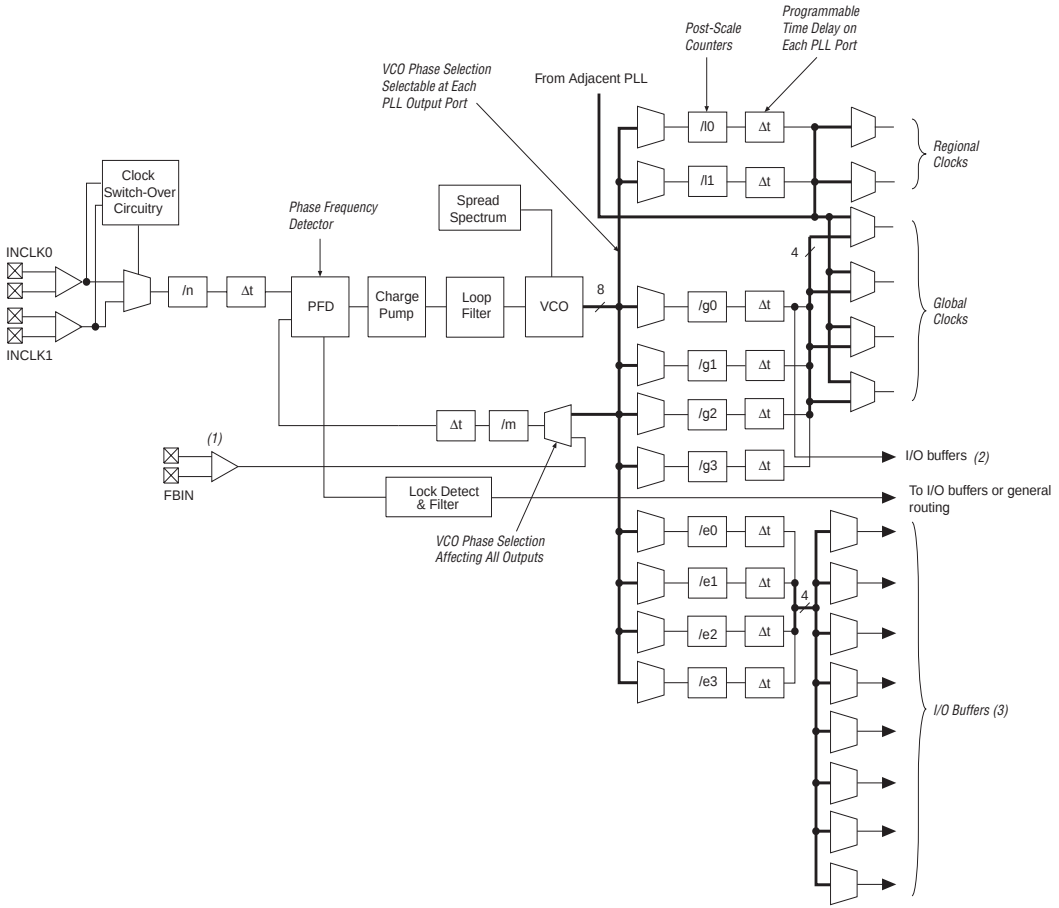
Figure 2–49. PLL Locations



Enhanced PLLs

Stratix devices contain up to four enhanced PLLs with advanced clock management features. Figure 2–52 shows a diagram of the enhanced PLL.

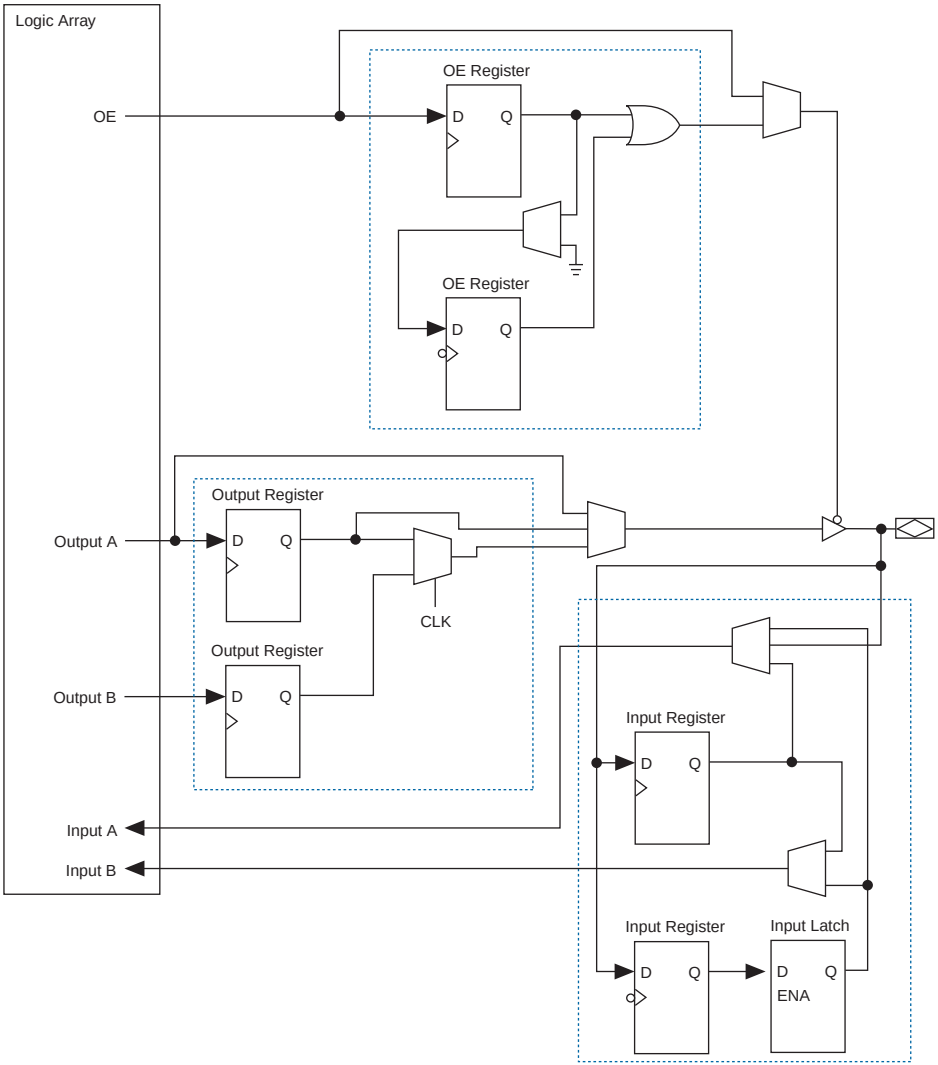
Figure 2–52. Stratix Enhanced PLL



Notes to Figure 2–52:

(1) External feedback is available in PLLs 5 and 6.
(2) This single-ended external output is available from the *g*0 counter for PLLs 11 and 12.
(3) These four counters and external outputs are available in PLLs 5 and 6.
(4) This connection is only available on EP1S40 and larger Stratix devices. For example, PLLs 5 and 11 are adjacent and PLLs 6 and 12 are adjacent. The EP1S40 device in the 780-pin FineLine BGA package does not support PLLs 11 and 12.

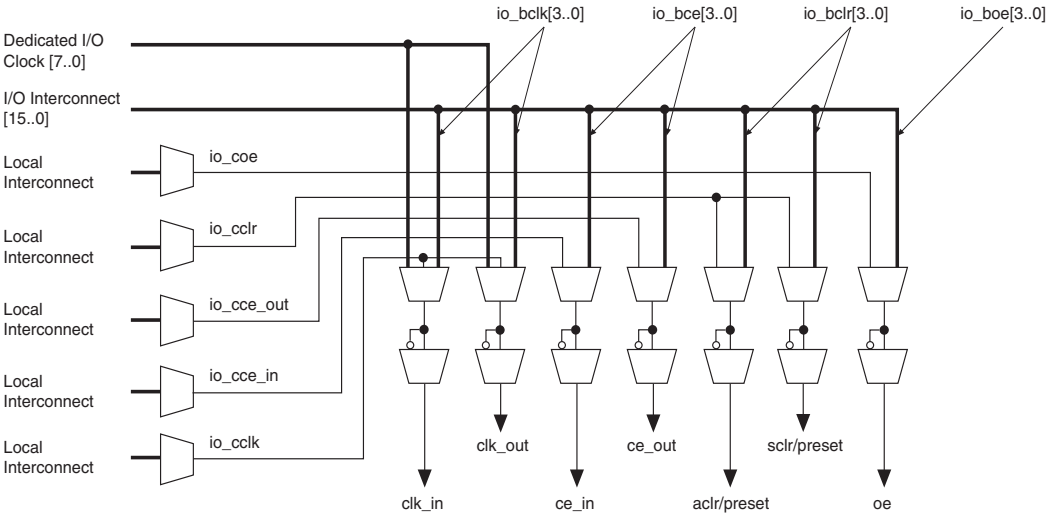
Figure 2–59. Stratix IOE Structure



The IOEs are located in I/O blocks around the periphery of the Stratix device. There are up to four IOEs per row I/O block and six IOEs per column I/O block. The row I/O blocks drive row, column, or direct link interconnects. The column I/O blocks drive column interconnects. Figure 2–60 shows how a row I/O block connects to the logic array. Figure 2–61 shows how a column I/O block connects to the logic array.

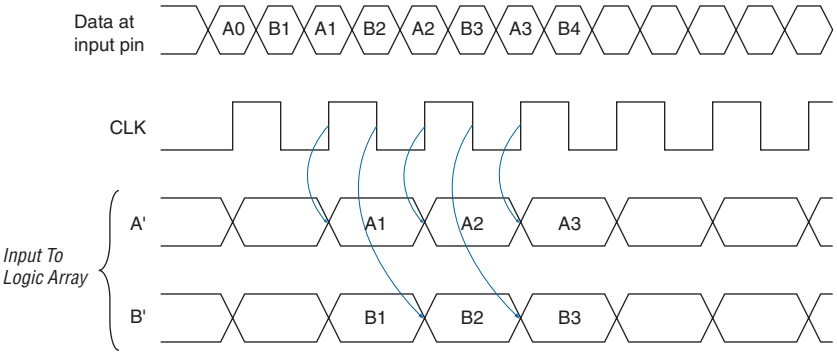
Each IOE contains its own control signal selection for the following control signals: oe, ce_in, ce_out, aclr/preset, sclr/preset, clk_in, and clk_out. Figure 2–63 illustrates the control signal selection.

Figure 2–63. Control Signal Selection per IOE



In normal bidirectional operation, the input register can be used for input data requiring fast setup times. The input register can have its own clock input and clock enable separate from the OE and output registers. The output register can be used for data requiring fast clock-to-output performance. The OE register can be used for fast clock-to-output enable timing. The OE and output register share the same clock source and the same clock enable source from local interconnect in the associated LAB, dedicated I/O clocks, and the column and row interconnects. Figure 2–64 shows the IOE in bidirectional configuration.

Figure 2–66. Input Timing Diagram in DDR Mode



When using the IOE for DDR outputs, the two output registers are configured to clock two data paths from LEs on rising clock edges. These output registers are multiplexed by the clock to drive the output pin at a ×2 rate. One output register clocks the first bit out on the clock high time, while the other output register clocks the second bit out on the clock low time. Figure 2–67 shows the IOE configured for DDR output. Figure 2–68 shows the DDR output timing diagram.

Tables 2–25 and 2–26 show the performance specification for DDR SDRAM, RLDRAM II, QDR SRAM, QDRII SRAM, and ZBT SRAM interfaces in EP1S10 through EP1S40 devices and in EP1S60 and EP1S80 devices. The DDR SDRAM and QDR SRAM numbers in Table 2–25 have been verified with hardware characterization with third-party DDR SDRAM and QDR SRAM devices over temperature and voltage extremes.

Table 2–25. External RAM Support in EP1S10 through EP1S40 Devices

DDR Memory Type	I/O Standard	Maximum Clock Rate (MHz)						
		-5 Speed Grade	-6 Speed Grade		-7 Speed Grade		-8 Speed Grade	
		Flip-Chip	Flip-Chip	Wire-Bond	Flip-Chip	Wire-Bond	Flip-Chip	Wire-Bond
DDR SDRAM *(1)*, *(2)*	SSTL-2	200	167	133	133	100	100	100
DDR SDRAM - side banks *(2)*, *(3)*, *(4)*	SSTL-2	150	133	110	133	100	100	100
RLDRAM II *(4)*	1.8-V HSTL	200	*(5)*	*(5)*	*(5)*	*(5)*	*(5)*	*(5)*
QDR SRAM *(6)*	1.5-V HSTL	167	167	133	133	100	100	100
QDRII SRAM *(6)*	1.5-V HSTL	200	167	133	133	100	100	100
ZBT SRAM *(7)*	LVTTL	200	200	200	167	167	133	133

Notes to Table 2–25:

(1) These maximum clock rates apply if the Stratix device uses DQS phase-shift circuitry to interface with DDR SDRAM. DQS phase-shift circuitry is only available in the top and bottom I/O banks (I/O banks 3, 4, 7, and 8).

(2) For more information on DDR SDRAM, see *AN 342: Interfacing DDR SDRAM with Stratix & Stratix GX Devices.*

(3) DDR SDRAM is supported on the Stratix device side I/O banks (I/O banks 1, 2, 5, and 6) without dedicated DQS phase-shift circuitry. The read DQS signal is ignored in this mode.

(4) These performance specifications are preliminary.

(5) This device does not support RLDRAM II.

(6) For more information on QDR or QDRII SRAM, see *AN 349: QDR SRAM Controller Reference Design for Stratix & Stratix GX Devices*.

(7) For more information on ZBT SRAM, see *AN 329: ZBT SRAM Controller Reference Design for Stratix & Stratix GX Devices*.

The output levels are compatible with systems of the same voltage as the power supply (i.e., when VCCIO pins are connected to a 1.5-V power supply, the output levels are compatible with 1.5-V systems). When VCCIO pins are connected to a 3.3-V power supply, the output high is 3.3 V and is compatible with 3.3-V or 5.0-V systems.

Table 2–36 summarizes Stratix MultiVolt I/O support.

Table 2–36. Stratix MultiVolt I/O Support Note (1)

V_{CCIO} (V)	Input Signal (5)					Output Signal (6)				
	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V	1.5 V	1.8 V	2.5 V	3.3 V	5.0 V
1.5	✓	✓	✓ (2)	✓ (2)		✓				
1.8	✓ (2)	✓	✓ (2)	✓ (2)		✓ (3)	✓			
2.5			✓	✓		✓ (3)	✓ (3)	✓		
3.3			✓ (2)	✓	✓ (4)	✓ (3)	✓ (3)	✓ (3)	✓	✓

Notes to Table 2–36:

(1) To drive inputs higher than V_{CCIO} but less than 4.1 V, disable the PCI clamping diode. However, to drive 5.0-V inputs to the device, enable the PCI clamping diode to prevent V_I from rising above 4.0 V.
(2) The input pin current may be slightly higher than the typical value.
(3) Although V_{CCIO} specifies the voltage necessary for the Stratix device to drive out, a receiving device powered at a different level can still interface with the Stratix device if it has inputs that tolerate the V_{CCIO} value.
(4) Stratix devices can be 5.0-V tolerant with the use of an external resistor and the internal PCI clamp diode.
(5) This is the external signal that is driving the Stratix device.
(6) This represents the system voltage that Stratix supports when a VCCIO pin is connected to a specific voltage level. For example, when VCCIO is 3.3 V and if the I/O standard is LVTTL/LVCMOS, the output high of the signal coming out from Stratix is 3.3 V and is compatible with 3.3-V or 5.0-V systems.

High-Speed Differential I/O Support

Stratix devices contain dedicated circuitry for supporting differential standards at speeds up to 840 Mbps. The following differential I/O standards are supported in the Stratix device: LVDS, LVPECL, HyperTransport, and 3.3-V PCML.

There are four dedicated high-speed PLLs in the EP1S10 to EP1S25 devices and eight dedicated high-speed PLLs in the EP1S30 to EP1S80 devices to multiply reference clocks and drive high-speed differential SERDES channels.

See the Stratix device pin-outs at **www.altera.com** for additional high speed DIFFIO pin information for Stratix devices.

The transmitter external clock output is transmitted on a data channel. The txclk pin for each bank is located in between data transmitter pins. For ×1 clocks (e.g., 622 Mbps, 622 MHz), the high-speed PLL clock bypasses the SERDES to drive the output pins. For half-rate clocks (e.g., 622 Mbps, 311 MHz) or any other even-numbered factor such as 1/4, 1/7, 1/8, or 1/10, the SERDES automatically generates the clock in the Quartus II software.

For systems that require more than four or eight high-speed differential I/O clock domains, a SERDES bypass implementation is possible using IOEs.

Byte Alignment

For high-speed source synchronous interfaces such as POS-PHY 4, XSBI, RapidIO, and HyperTransport technology, the source synchronous clock rate is not a byte- or SERDES-rate multiple of the data rate. Byte alignment is necessary for these protocols since the source synchronous clock does not provide a byte or word boundary since the clock is one half the data rate, not one eighth. The Stratix device's high-speed differential I/O circuitry provides dedicated data realignment circuitry for user-controlled byte boundary shifting. This simplifies designs while saving LE resources. An input signal to each fast PLL can stall deserializer parallel data outputs by one bit period. You can use an LE-based state machine to signal the shift of receiver byte boundaries until a specified pattern is detected to indicate byte alignment.

Power Sequencing & Hot Socketing

Because Stratix devices can be used in a mixed-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. Therefore, the VCCIO and VCCINT power supplies may be powered in any order.

Although you can power up or down the VCCIO and VCCINT power supplies in any sequence, you should not power down any I/O banks that contain configuration pins while leaving other I/O banks powered on. For power up and power down, all supplies (VCCINT and all VCCIO power planes) must be powered up and down within 100 ms of each other. This prevents I/O pins from driving out.

Signals can be driven into Stratix devices before and during power up without damaging the device. In addition, Stratix devices do not drive out during power up. Once operating conditions are reached and the device is configured, Stratix devices operate as specified by the user. For more information, see *Hot Socketing* in the *Selectable I/O Standards in Stratix & Stratix GX Devices* chapter in the *Stratix Device Handbook, Volume 2*.

For Stratix, the CRC is computed by the Quartus II software and downloaded into the device as a part of the configuration bit stream. The CRC_ERROR pin reports a soft error when configuration SRAM data is corrupted, triggering device reconfiguration.

Custom-Built Circuitry

Dedicated circuitry is built in the Stratix devices to perform error detection automatically. You can use the built-in dedicated circuitry for error detection using CRC feature in Stratix devices, eliminating the need for external logic. This circuitry will perform error detection automatically when enabled. This error detection circuitry in Stratix devices constantly checks for errors in the configuration SRAM cells while the device is in user mode. You can monitor one external pin for the error and use it to trigger a re-configuration cycle. Select the desired time between checks by adjusting a built-in clock divider.

Software Interface

In the Quartus II software version 4.1 and later, you can turn on the automated error detection CRC feature in the **Device & Pin Options** dialog box. This dialog box allows you to enable the feature and set the internal frequency of the CRC between 400 kHz to 100 MHz. This controls the rate that the CRC circuitry verifies the internal configuration SRAM bits in the FPGA device.

For more information on CRC, see *AN 357: Error Detection Using CRC in Altera FPGA Devices*.

Temperature Sensing Diode

Stratix devices include a diode-connected transistor for use as a temperature sensor in power management. This diode is used with an external digital thermometer device such as a MAX1617A or MAX1619 from MAXIM Integrated Products. These devices steer bias current through the Stratix diode, measuring forward voltage and converting this reading to temperature in the form of an 8-bit signed number (7 bits plus sign). The external device's output represents the junction temperature of the Stratix device and can be used for intelligent power management.

The diode requires two pins (tempdiodep and tempdioden) on the Stratix device to connect to the external temperature-sensing device, as shown in Figure 3–5. The temperature sensing diode is a passive element and therefore can be used before the Stratix device is powered.

Table 4–36. Stratix Performance (Part 2 of 2) Notes (1), (2)

Applications		Resources Used			Performance				
		LEs	TriMatrix Memory Blocks	DSP Blocks	-5 Speed Grade	-6 Speed Grade	-7 Speed Grade	-8 Speed Grade	Units
TriMatrix memory M-RAM block	True dual-port RAM 16K × 36 bit	0	1	0	269.83	237.69	206.82	175.74	MHz
	Single port RAM 32K × 18 bit	0	1	0	275.86	244.55	212.76	180.83	MHz
	Simple dual-port RAM 32K × 18 bit	0	1	0	275.86	244.55	212.76	180.83	MHz
	True dual-port RAM 32K × 18 bit	0	1	0	275.86	244.55	212.76	180.83	MHz
	Single port RAM 64K × 9 bit	0	1	0	287.85	253.29	220.36	187.26	MHz
	Simple dual-port RAM 64K × 9 bit	0	1	0	287.85	253.29	220.36	187.26	MHz
	True dual-port RAM 64K × 9 bit	0	1	0	287.85	253.29	220.36	187.26	MHz
DSP block	9 × 9-bit multiplier *(3)*	0	0	1	335.0	293.94	255.68	217.24	MHz
	18 × 18-bit multiplier *(4)*	0	0	1	278.78	237.41	206.52	175.50	MHz
	36 × 36-bit multiplier *(4)*	0	0	1	148.25	134.71	117.16	99.59	MHz
	36 × 36-bit multiplier *(5)*	0	0	1	278.78	237.41	206.52	175.5	MHz
	18-bit, 4-tap FIR filter	0	0	1	278.78	237.41	206.52	175.50	MHz
Larger Designs	8-bit, 16-tap parallel FIR filter	58	0	4	141.26	133.49	114.88	100.28	MHz
	8-bit, 1,024-point FFT function	870	5	1	261.09	235.51	205.21	175.22	MHz

Notes to Table 4–36:

(1) These design performance numbers were obtained using the Quartus II software.
(2) Numbers not listed will be included in a future version of the data sheet.
(3) This application uses registered inputs and outputs.
(4) This application uses registered multiplier input and output stages within the DSP block.
(5) This application uses registered multiplier input, pipeline, and output stages within the DSP block.

Internal Timing Parameters

Internal timing parameters are specified on a speed grade basis independent of device density. Tables 4–37 through 4–42 describe the Stratix device internal timing microparameters for LEs, IOEs, TriMatrix™ memory structures, DSP blocks, and MultiTrack interconnects.

Table 4–37. LE Internal Timing Microparameter Descriptions

Symbol	Parameter
t_{SU}	LE register setup time before clock
t_{H}	LE register hold time after clock
t_{CO}	LE register clock-to-output delay
t_{LUT}	LE combinatorial LUT delay for data-in to data-out
t_{CLR}	Minimum clear pulse width
t_{PRE}	Minimum preset pulse width
t_{CLKHL}	Register minimum clock high or low time. The maximum core clock frequency can be calculated by $1/(2 \times t_{CLKHL})$.

Table 4–38. IOE Internal Timing Microparameter Descriptions

Symbol	Parameter
t_{SU_R}	Row IOE input register setup time
t_{SU_C}	Column IOE input register setup time
t_{H}	IOE input and output register hold time after clock
t_{CO_R}	Row IOE input and output register clock-to-output delay
t_{CO_C}	Column IOE input and output register clock-to-output delay
$t_{PIN2COMBOUT\_R}$	Row input pin to IOE combinatorial output
$t_{PIN2COMBOUT\_C}$	Column input pin to IOE combinatorial output
$t_{COMBIN2PIN\_R}$	Row IOE data input to combinatorial output pin
$t_{COMBIN2PIN\_C}$	Column IOE data input to combinatorial output pin
t_{CLR}	Minimum clear pulse width
t_{PRE}	Minimum preset pulse width
t_{CLKHL}	Register minimum clock high or low time. The maximum I/O clock frequency can be calculated by $1/(2 \times t_{CLKHL})$. Performance may also be affected by I/O timing, use of PLL, and I/O programmable settings.

Table 4–114. Stratix Maximum Input Clock Rate for CLK[7..4] & CLK[15..12] Pins in Flip-Chip Packages (Part 2 of 2)

I/O Standard	-5 Speed Grade	-6 Speed Grade	-7 Speed Grade	-8 Speed Grade	Unit
LVDS *(1)*	645	645	622	622	MHz
HyperTransport technology *(1)*	500	500	450	450	MHz

Table 4–115. Stratix Maximum Input Clock Rate for CLK[0, 2, 9, 11] Pins & FPLL[10..7]CLK Pins in Flip-Chip Packages

I/O Standard	-5 Speed Grade	-6 Speed Grade	-7 Speed Grade	-8 Speed Grade	Unit
LVTTL	422	422	390	390	MHz
2.5 V	422	422	390	390	MHz
1.8 V	422	422	390	390	MHz
1.5 V	422	422	390	390	MHz
LVCMOS	422	422	390	390	MHz
GTL+	300	250	200	200	MHz
SSTL-3 Class I	400	350	300	300	MHz
SSTL-3 Class II	400	350	300	300	MHz
SSTL-2 Class I	400	350	300	300	MHz
SSTL-2 Class II	400	350	300	300	MHz
SSTL-18 Class I	400	350	300	300	MHz
SSTL-18 Class II	400	350	300	300	MHz
1.5-V HSTL Class I	400	350	300	300	MHz
1.8-V HSTL Class I	400	350	300	300	MHz
CTT	300	250	200	200	MHz
Differential 1.5-V HSTL C1	400	350	300	300	MHz
LVPECL *(1)*	717	717	640	640	MHz
PCML *(1)*	400	375	350	350	MHz
LVDS *(1)*	717	717	640	640	MHz
HyperTransport technology *(1)*	717	717	640	640	MHz

Table 4–125. High-Speed I/O Specifications for Flip-Chip Packages (Part 2 of 4) Notes (1), (2)

Symbol	Conditions	-5 Speed Grade			-6 Speed Grade			-7 Speed Grade			-8 Speed Grade			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f_{HSCLK} (Clock frequency) (PCML) $f_{HSCLK} = f_{HSDR} / W$	*W* = 4 to 30 (Serdes used)	10		100	10		100	10		77.75	10		77.75	MHz
	W = 2 (Serdes bypass)	50		200	50		200	50		150	50		150	MHz
	W = 2 (Serdes used)	150		200	150		200	150		155.5	150		155.5	MHz
	W = 1 (Serdes bypass)	100		250	100		250	100		200	100		200	MHz
	W = 1 (Serdes used)	300		400	300		400	300		311	300		311	MHz
f_{HSDR} Device operation (PCML)	*J* = 10	300		400	300		400	300		311	300		311	Mbps
	J = 8	300		400	300		400	300		311	300		311	Mbps
	J = 7	300		400	300		400	300		311	300		311	Mbps
	J = 4	300		400	300		400	300		311	300		311	Mbps
	J = 2	100		400	100		400	100		300	100		300	Mbps
	J = 1	100		250	100		250	100		200	100		200	Mbps
TCCS	All			200			200			300			300	ps

E